

RELIABILITY REPORT  
FOR

**DS1626 A2**

**Dallas Semiconductor**

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Prepared by:

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**Conclusion:**

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

DS1626 A2

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at <http://www.maxim-ic.com/TechSupport/dsreliability.html>.

**Device Description:**

A description of this device can be found in the product data sheet. You can find the product data sheet at [http://dbserv.maxim-ic.com/l\\_datasheet3.cfm](http://dbserv.maxim-ic.com/l_datasheet3.cfm).

**Reliability Derating:**

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

$$AfT = \exp((Ea/k) * (1/Tu - 1/Ts)) = tu/ts$$

AfT = Acceleration factor due to Temperature  
tu = Time at use temperature (e.g. 55°C)  
ts = Time at stress temperature (e.g. 125°C)  
k = Boltzmann's Constant (8.617 x 10<sup>-5</sup> eV/°K)  
Tu = Temperature at Use (°K)  
Ts = Temperature at Stress (°K)  
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

$$AfV = \exp(B * (Vs - Vu))$$

AfV = Acceleration factor due to Voltage  
Vs = Stress Voltage (e.g. 7.0 volts)  
Vu = Maximum Operating Voltage (e.g. 5.5 volts)  
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

$$Fr = X / (ts * AfV * AfT * N * 2)$$

X = Chi-Sq statistical upper limit  
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

$$MTTF = 1/Fr$$

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

**FAILURE RATE:**                      **MTTF (YRS): 65215**                      **FITS: 1.8**

The parameters used to calculate this failure rate are as follows:

**Cf: 60%**                      **Ea: 0.7**                      **B: 0**                      **Tu: 25 °C**                      **Vu: 5.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available.

**Device Information:**

Process: D6W-2P2M,HPVt,E2,EPROGVt,TCN1 PBL:GOI  
 Passivation: Passivation w/Nov TEOS Oxide-Nitride  
 Die Size: 71 x 54  
 Number of Transistors: 7815  
 Interconnect: Aluminum / 1% Silicon / 0.5% Copper  
 Gate Oxide Thickness: 150 Å

**ELECTRICAL CHARACTERIZATION**

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS
ESD SENSITIVITY	0248	EOS/ESD S5.1 HBM 500 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0248	EOS/ESD S5.1 HBM 1000 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0248	EOS/ESD S5.1 HBM 2000 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0248	EOS/ESD S5.1 HBM 4000 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0248	EOS/ESD S5.1 HBM 8000 VOLTS	1 PUL'S	3	1
LATCH-UP	0248	JESD78, I-TEST 125C		6	0
LATCH-UP	0248	JESD78, Vsupply TEST 125C		6	0
<b>Total:</b>					<b>1</b>

**OPERATING LIFE**

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS
HIGH TEMP OP LIFE	0221	125C, 5.25 VOLTS	1000 HRS	45	0
HIGH VOLTAGE LIFE	0223	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH VOLTAGE LIFE	0223	125C, 6.0 VOLTS	1000 HRS	80	0
HIGH VOLTAGE LIFE	0226	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH VOLTAGE LIFE	0245	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH VOLTAGE LIFE	0248	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH VOLTAGE LIFE	0249	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0312	125C, 5.5 VOLTS	1000 HRS	45	0

**Total: 0**

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**STORAGE LIFE**

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS
STORAGE LIFE	0226	150C	1000 HRS	77	0
<b>Total:</b>					<b>0</b>

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**W/E ENDURANCE AND DATA RET'N**

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS
WRITE CYCLE STRESS	0223	85 C, 6.0 VOLTS	25 KCYS	77	0
STORAGE LIFE		150C	1336 HRS	77	0
WRITE CYCLE STRESS	0223	85 C, 6.0 VOLTS	10 KCYS	77	0
STORAGE LIFE		150C	1000 HRS	76	0
WRITE CYCLE STRESS	0245	70 C, 5.5 VOLTS	30 KCYS	77	0
STORAGE LIFE		150C	1000 HRS	73	0
WRITE CYCLE STRESS	0248	85 C, 6.0 VOLTS	30 KCYS	77	0
STORAGE LIFE		150C	1000 HRS	77	0
WRITE CYCLE STRESS	0249	70 C, 5.5 VOLTS	30 KCYS	77	0
STORAGE LIFE		150C	1000 HRS	77	1
WRITE CYCLE STRESS	0312	85 C, 5.5 VOLTS	30 KCYS	77	0
STORAGE LIFE		150C	1000 HRS	72	0
<b>Total:</b>					<b>1</b>

**FAILURE RATE:**

**MTTF (YRS): 65215**

**FITS: 1.8**